

Title (en)

POLYOXOMETALLATES IN MEMORY DEVICES

Title (de)

POLYOXOMETALLATE IN SPEICHERVORRICHTUNGEN

Title (fr)

POLYOXOMETALLATES DANS DES DISPOSITIFS DE MEMOIRE

Publication

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Application

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Abstract (en)

[origin: WO2007015010A1] The invention relates to a DRAM memory device with a capacity associated with a field effect transistor, in which all or some of the molecules capable of storing the loads comprising a polyoxometallate are incorporated into the capacity, or a Flash-type memory using at least one field effect transistor, in which the molecules capable of storing the loads comprising a polyoxometallate are incorporated into the floating grid of the transistor. The invention also relates to a method for producing one such device and to an electronic appliance comprising one such memory device.

IPC 8 full level

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